L Number	Hits	Search Text	DB	Time stamp
	4	09/948879	USPAT	2004/03/05 09:47
-	0	10/278551	USPAT	2004/03/04 16:43
-	1	("5998833").PN.	USPAT	2004/03/05 09:47
-	1	("5917216").PN.	USPAT	2004/03/05 09:47
-	1	("5514608").PN.	USPAT	2004/03/05 09:48
-	0	(high adj voltage adj transistor) and (field adj plate) and	USPAT	2004/03/05 09:50
		trench and spaced-part and trenches and epitaxial		
-	97	(high adj voltage adj transistor) and (field adj plate)	USPAT	2004/03/05 09:50
.	1	(high adj voltage adj transistor) and (field adj plate) and (pair	USPAT	2004/03/05 09:53
i		adj2 spaced adj apart adj trenches)		
-	1197	438/197	USPAT	2004/03/05 09:53
-	893	438/270	USPAT	2004/03/05 09:53
۱.	535	438/309	USPAT	2004/03/05 09:53
-	310	438/311	USPAT	2004/03/05 09:53
l -	93	438/316	USPAT	2004/03/05 09:53
-	98	438/414	USPAT	2004/03/05 09:53
] -	284	438/529	USPAT	2004/03/05 09:53
† -	511	438/589	USPAT	2004/03/05 09:53
-	75	438/914	USPAT	2004/03/05 09:54
-	1	(("5998833").PN.) and (field or plate or members or trnch	USPAT	2004/03/05 09:56
		or trenches or apart or spaced or sidewall or potion or		
		dielectric or covering or drain or region or source or		
		extended or substrate or epitaxial or high or voltage or		
		remaining or transistor)		